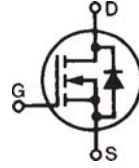


Linear™ Power MOSFET IXTH24N50L

w/ Extended FBSOA

N-Channel Enhancement Mode
Avalanche Rated



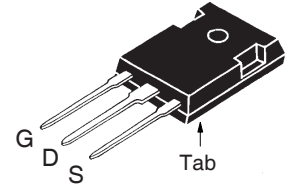
$$V_{DSS} = 500V$$

$$I_{D25} = 24A$$

$$R_{DS(on)} \leq 300m\Omega$$

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 500 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 24 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 50 | A |
| I_A | $T_C = 25^\circ C$ | 12 | A |
| E_{AS} | $T_C = 25^\circ C$ | 1.5 | J |
| P_D | $T_C = 25^\circ C$ | 400 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | 1.6mm (0.062in.) from Case for 10s | 300 | $^\circ C$ |
| T_{sold} | Plastic Body for 10 seconds | 260 | $^\circ C$ |
| M_d | Mounting Torque | 1.13 / 10 | Nm/lb.in. |
| Weight | | 6 | g |

TO-247



G = Gate D = Drain
S = Source Tab = Drain

Features

- Designed for Linear Operation
- International Standard Package
- Avalanche Rated
- Molding Epoxy Meets UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Programmable Loads
- Current Regulators
- DC-DC Converters
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 3.5 | | 6.0 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 50 μA 500 μA |
| $R_{DS(on)}$ | $V_{GS} = 20V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 300 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | | |
|--------------|--|-----------------------|------|------|--------------------|
| | | Min. | Typ. | Max. | |
| g_{fs} | $V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 3 | 7 | 11 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 2500 | | pF |
| C_{oss} | | | 400 | | pF |
| C_{rss} | | | 100 | | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\Omega$ (External) | | 35 | | ns |
| t_r | | | 85 | | ns |
| $t_{d(off)}$ | | | 110 | | ns |
| t_f | | | 75 | | ns |
| $Q_{g(on)}$ | $V_{GS} = 20\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 160 | | nC |
| Q_{gs} | | | 30 | | nC |
| Q_{gd} | | | 50 | | nC |
| R_{thJC} | | | | 0.31 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.21 | | | $^\circ\text{C/W}$ |

Safe-Operating-Area Specification

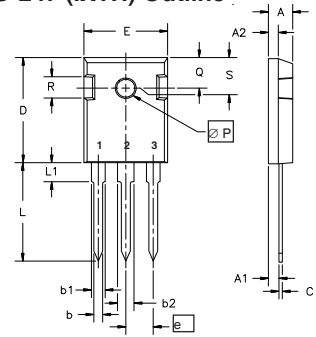
| Symbol | Test Conditions | Characteristic Values | | | |
|--------|---|-----------------------|------|------|---|
| | | Min. | Typ. | Max. | |
| SOA | $V_{DS} = 400\text{V}$, $I_D = 0.5\text{A}$, $T_C = 60^\circ\text{C}$ | 200 | | | W |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | | |
|----------|--|-----------------------|------|------|----|
| | | Min. | Typ. | Max. | |
| I_S | $V_{GS} = 0\text{V}$ | | | 24 | A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 96 | A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.5 | V |
| t_{rr} | $I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$ | | 500 | | ns |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | .242 | BSC |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics
@ $T_J = 25^\circ\text{C}$

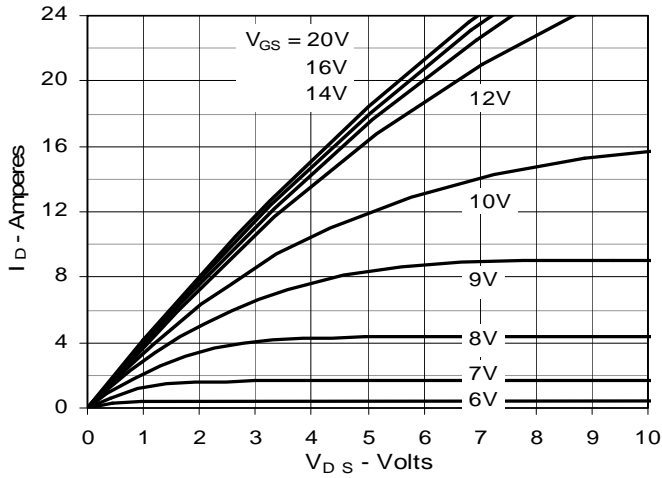


Fig. 2. Extended Output Characteristics
@ $T_J = 25^\circ\text{C}$

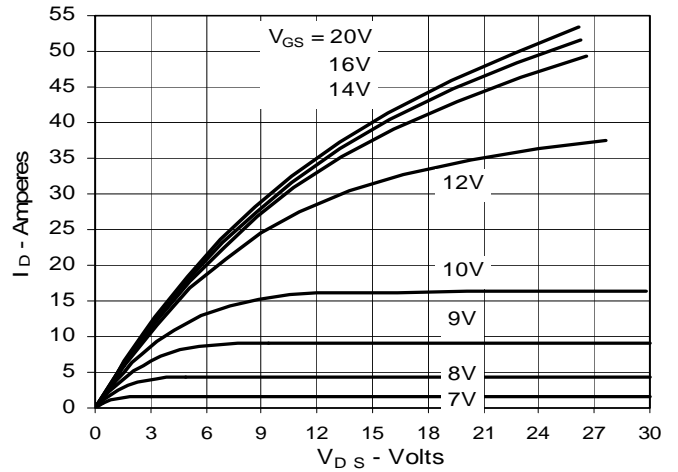


Fig. 3. Output Characteristics
@ $T_J = 125^\circ\text{C}$

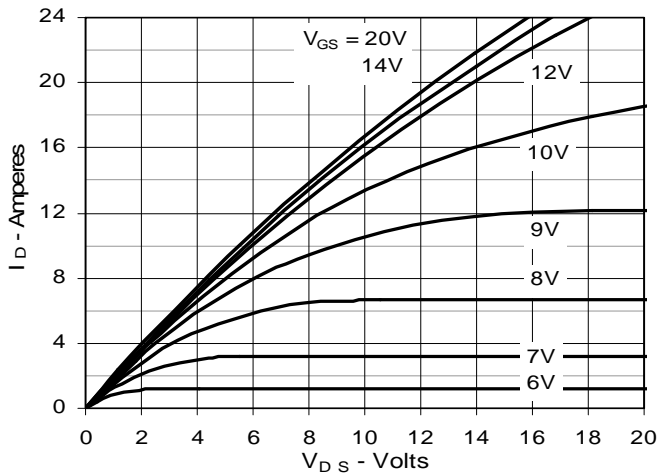


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

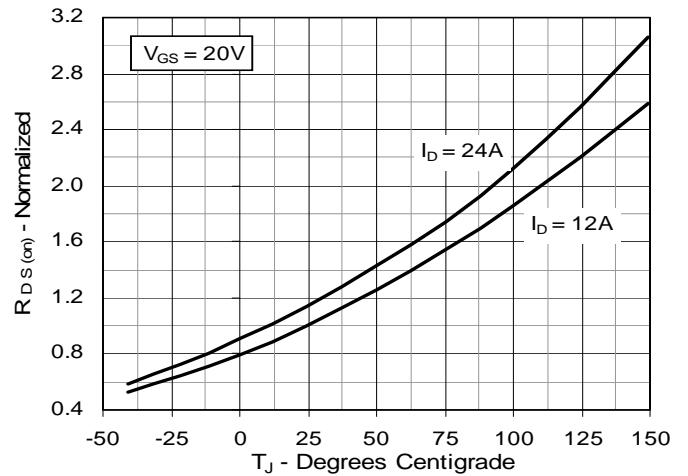


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

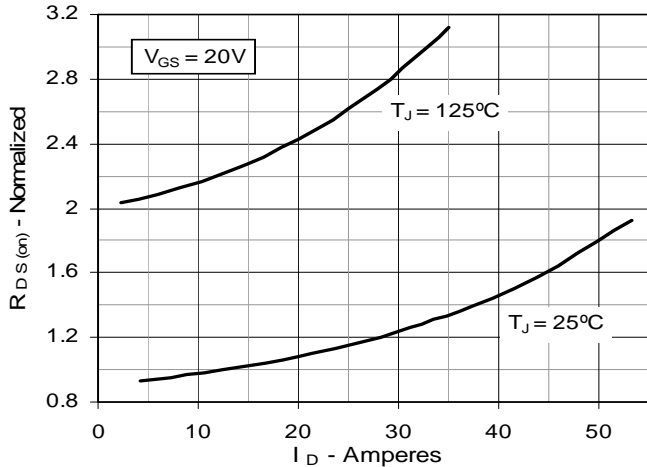


Fig. 6. Drain Current vs. Case Temperature

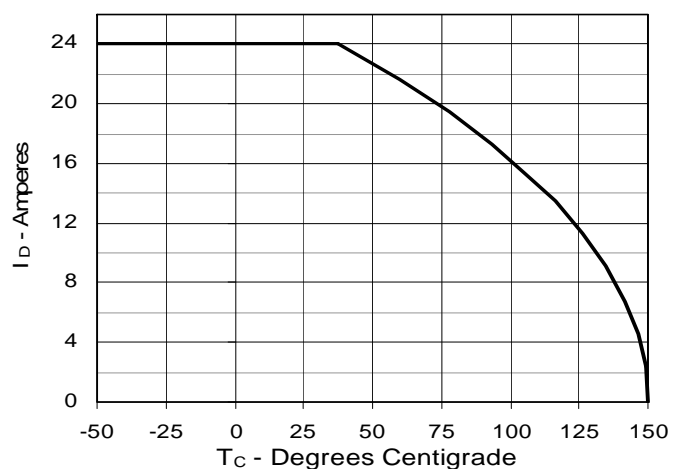


Fig. 7. Input Admittance

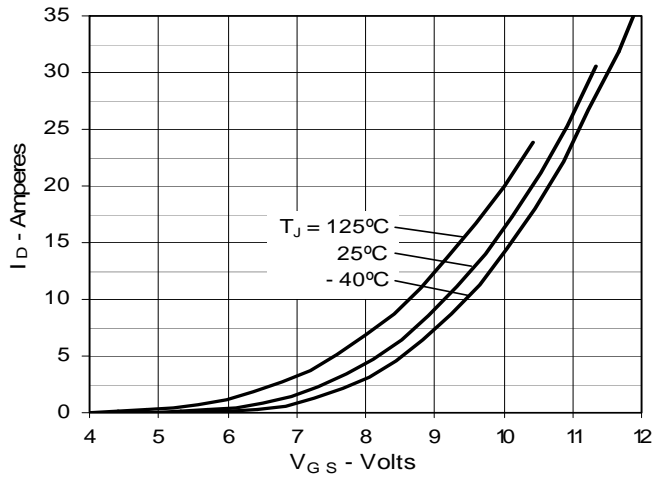


Fig. 8. Transconductance

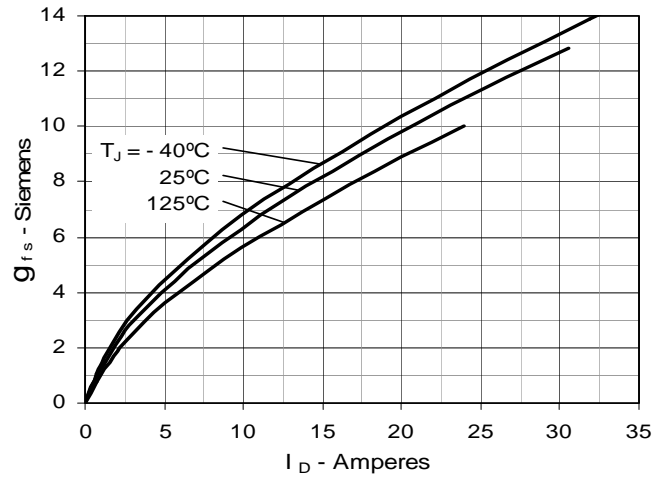


Fig. 9. Source Current vs. Source-To-Drain Voltage

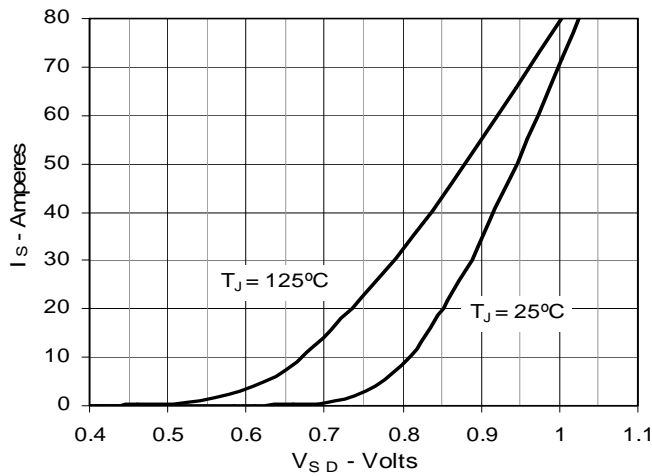


Fig. 10. Gate Charge

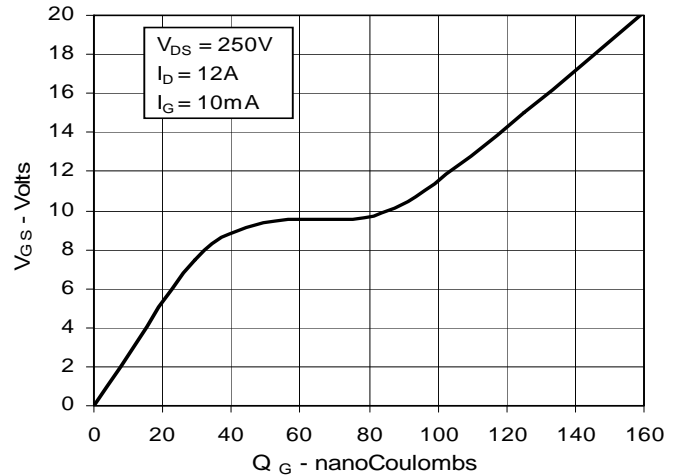


Fig. 11. Capacitance

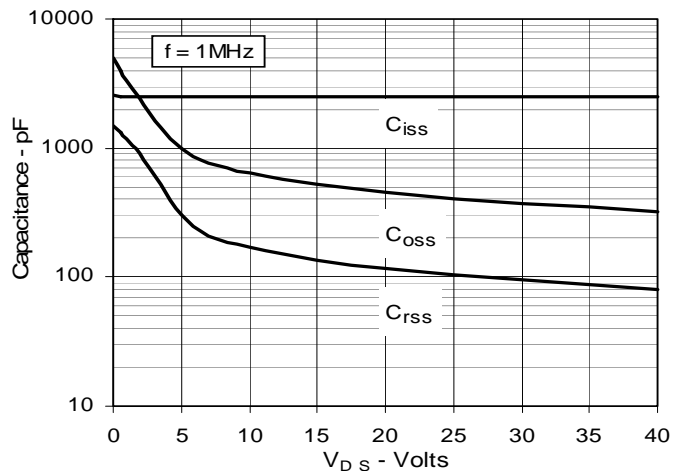


Fig. 12. Maximum Transient Thermal Impedance

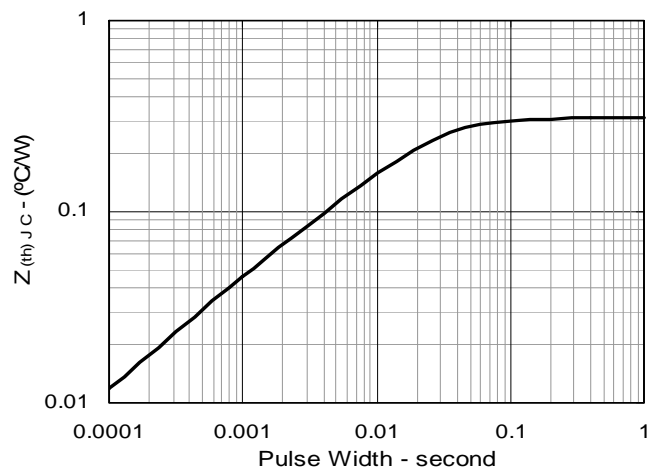


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

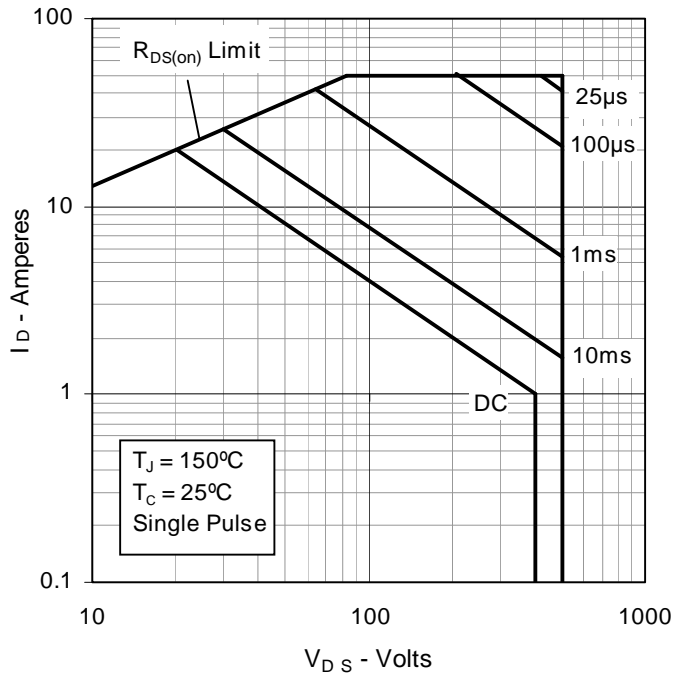
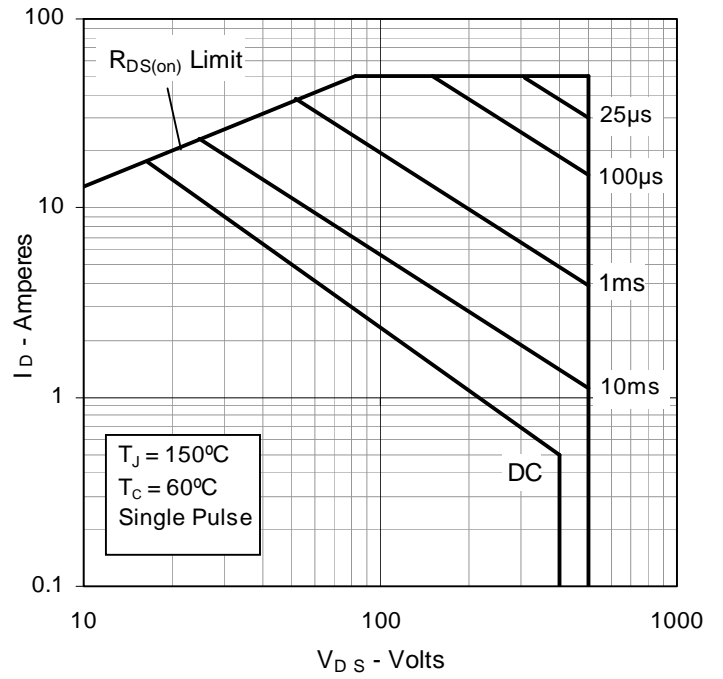


Fig. 14. Forward-Bias Safe Operating Area @ $T_C = 60^\circ\text{C}$





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